

N-Channel Enhancement-Mode MOSFET

DESIGNED FOR:

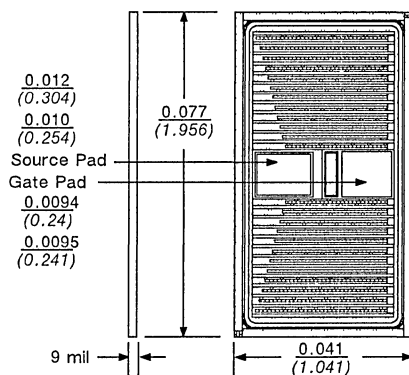
- Switching

FEATURES

- High Speed for Military Applications
(see VNDQ09 for Industrial Applications)

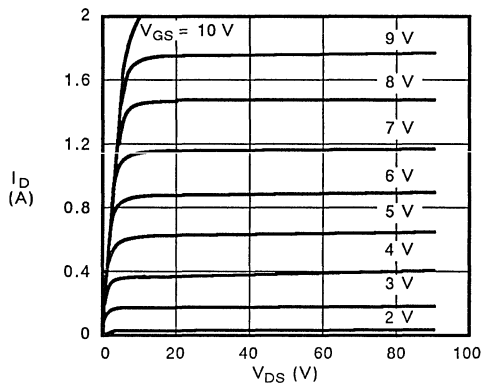
TYPE	PACKAGE	DEVICE
Single	TO-205AD	• JANTX2N6661

GEOMETRY DIAGRAM

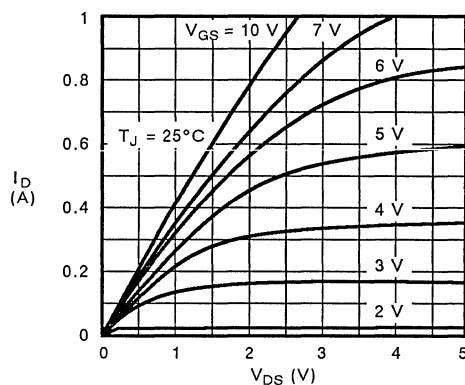


TYPICAL CHARACTERISTICS

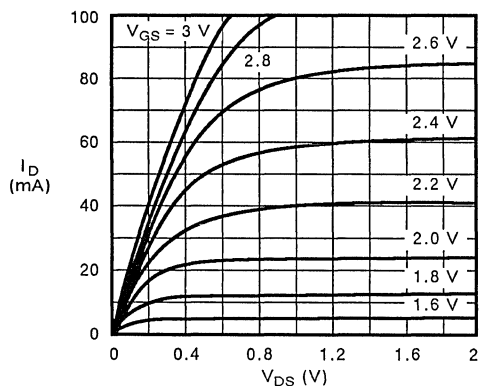
Output Characteristics



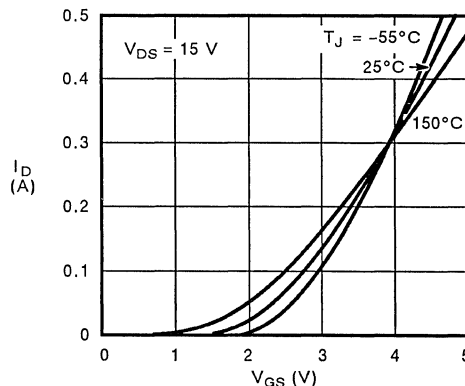
Ohmic Region Characteristics



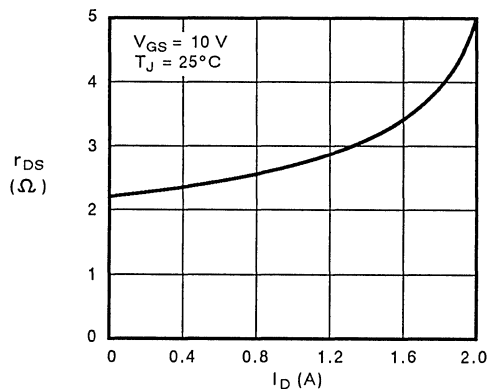
Output Characteristics for Low Gate Drive



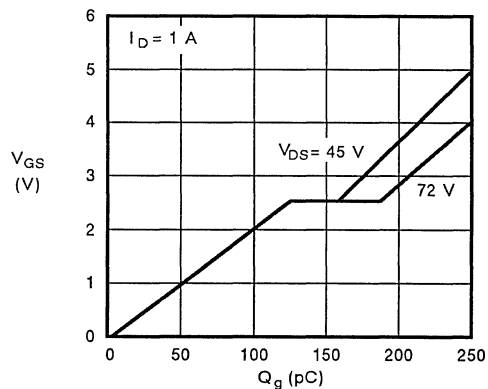
Transfer Characteristics



On-Resistance

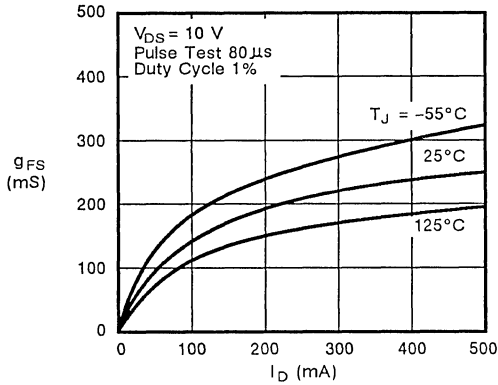


Gate Charge

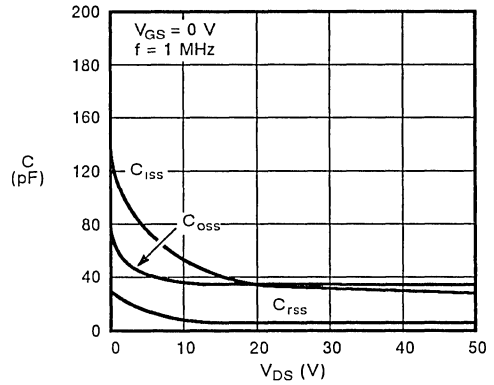


TYPICAL CHARACTERISTICS

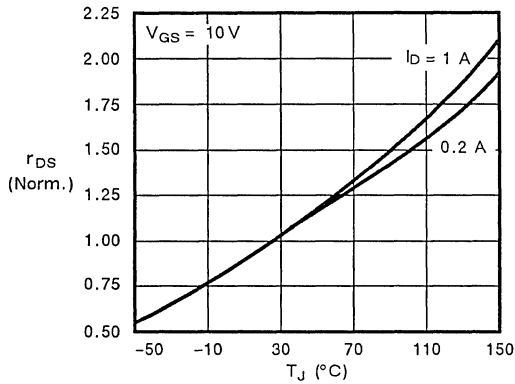
Transconductance



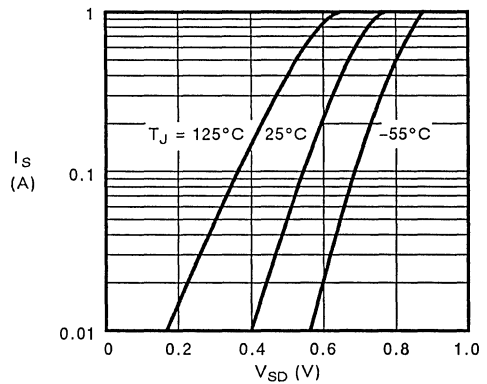
Capacitance



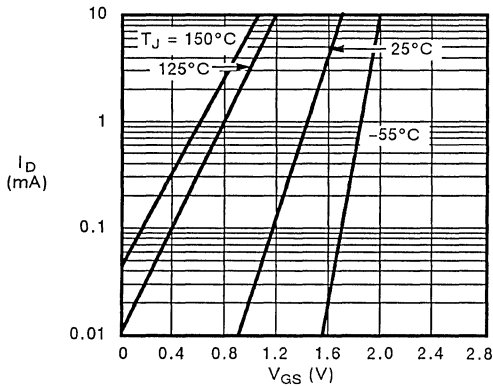
On-Resistance vs. Junction Temperature



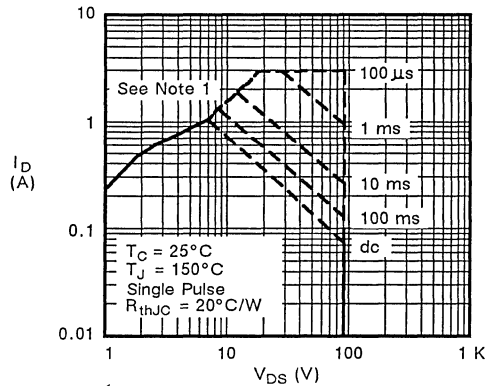
Source-Drain Diode Forward Voltage



Threshold Region

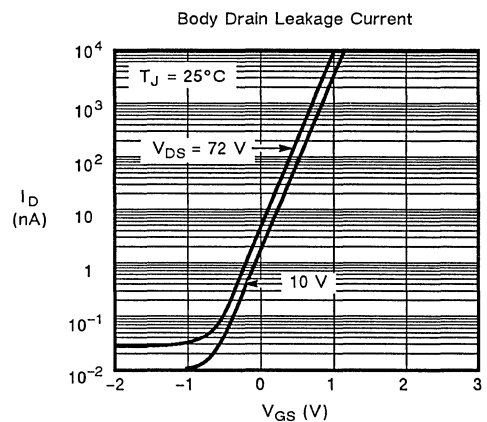
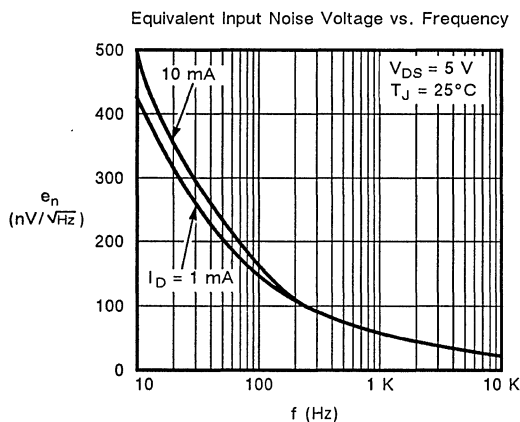
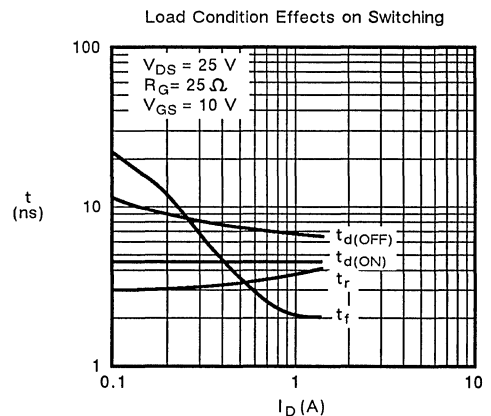
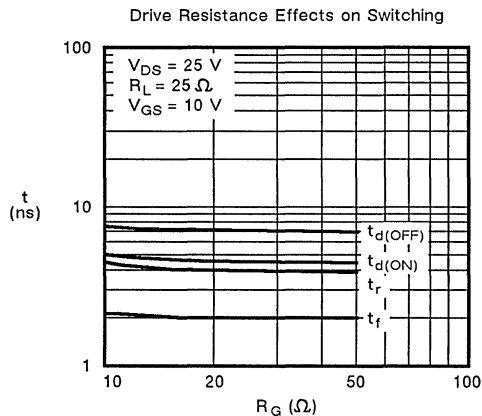
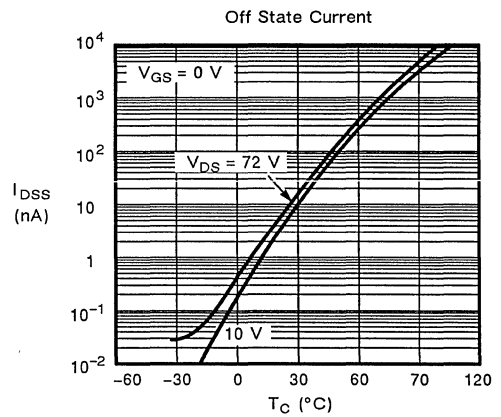
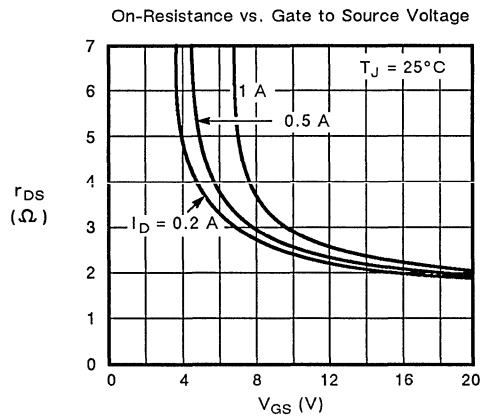


Safe Operating Area



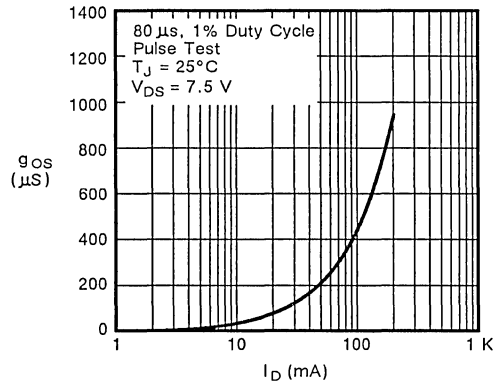
¹Operation in this area may be limited by $r_{DS(ON)}$

TYPICAL CHARACTERISTICS



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Output Conductance vs. Drain Current



Transient Thermal Response (TO-39)

